

ABSTRACT

A semiconductor laser device with two active-layer stripe structures has an n-InP substrate (1), an n-InP clad layer (2), a lower GRIN-SCH layer (3b), an active layer (4b), an upper GRIN-SCH layer (5b), a p-InP clad layer (6), and a p-InGaAsP contact layer (7) laminated in this order, in a side cross section including one of the stripe structure. A high-reflection film (12) is disposed on a reflection-side end surface, and a low-reflection film (13) is disposed on an emission-side end surface. A p-side electrode (8b) is disposed on only a part of the upper surface of the p-InGaAsP contact layer (7) so that a current non-injection area (14) is formed on the rest of the area.